

# EECS 151/251A

## SP2022 Discussion 11

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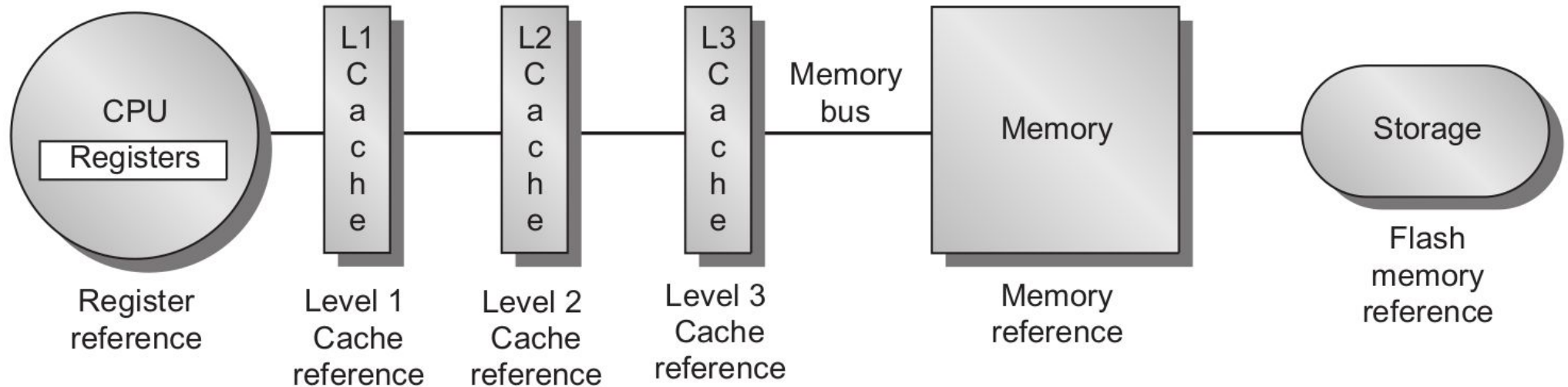
# Agenda

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- Caches
- SRAM Decoders
- Other Memories (DRAM, CAM, Flash)

# Caches

# Memory Hierarchy Overview



<b>Laptop</b>	Size:	1000 bytes	64 KB	256 KB	4-8 MB	4–16 GB	256 GB-1 TB
	Speed:	300 ps	1 ns	3–10 ns	10–20 ns	50–100 ns	50-100 $\mu$ S
<b>Desktop</b>	Size:	2000 bytes	64 KB	256 KB	8-32 MB	8–64 GB	256 GB-2 TB
	Speed:	300 ps	1 ns	3–10 ns	10–20 ns	50–100 ns	50-100 $\mu$ S

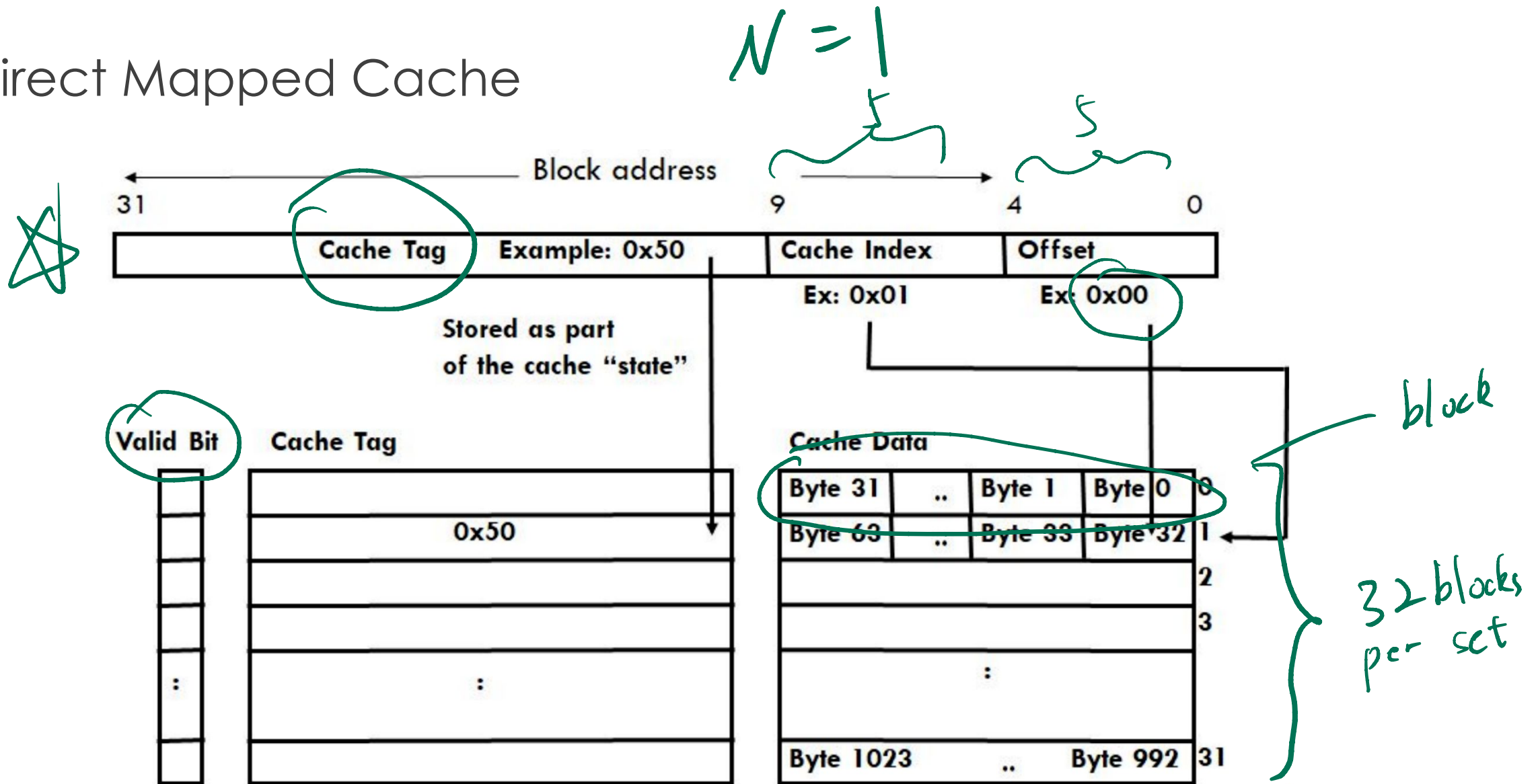
(B) Memory hierarchy for a laptop or a desktop

Hennessy, John L., and David A. Patterson. *Computer architecture: a quantitative approach*. Elsevier, 2011.

# What is a Cache?

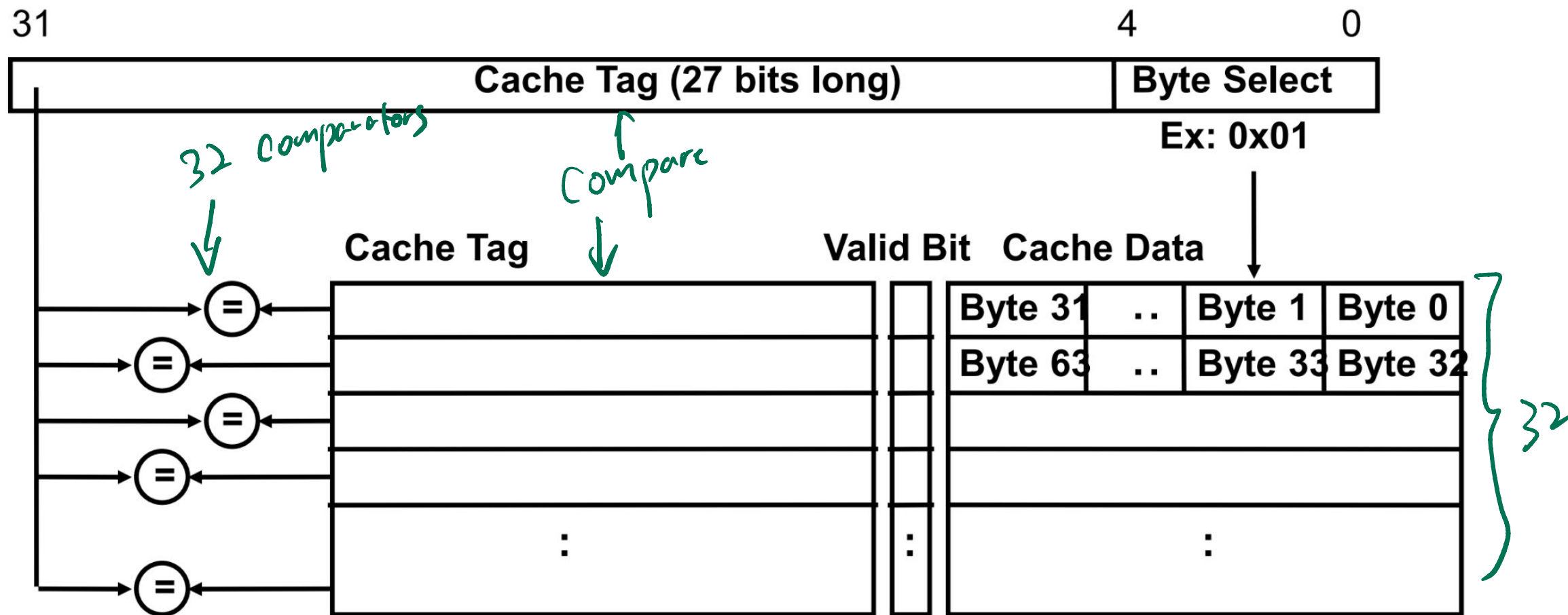
- A cache holds commonly used memory data.
- An **ideal cache** would anticipate all of the data needed by CPU, and fetch it from main memory ahead of time, so that it has zero miss rate.
- Caches are specified by:
  - C: capacity
  - b: block size: Granularity of memory loaded into cache
  - B: number of blocks ( $B = C / b$ )
  - S: number of sets
  - N: degree of associativity

# Direct Mapped Cache



# Fully Associative Cache

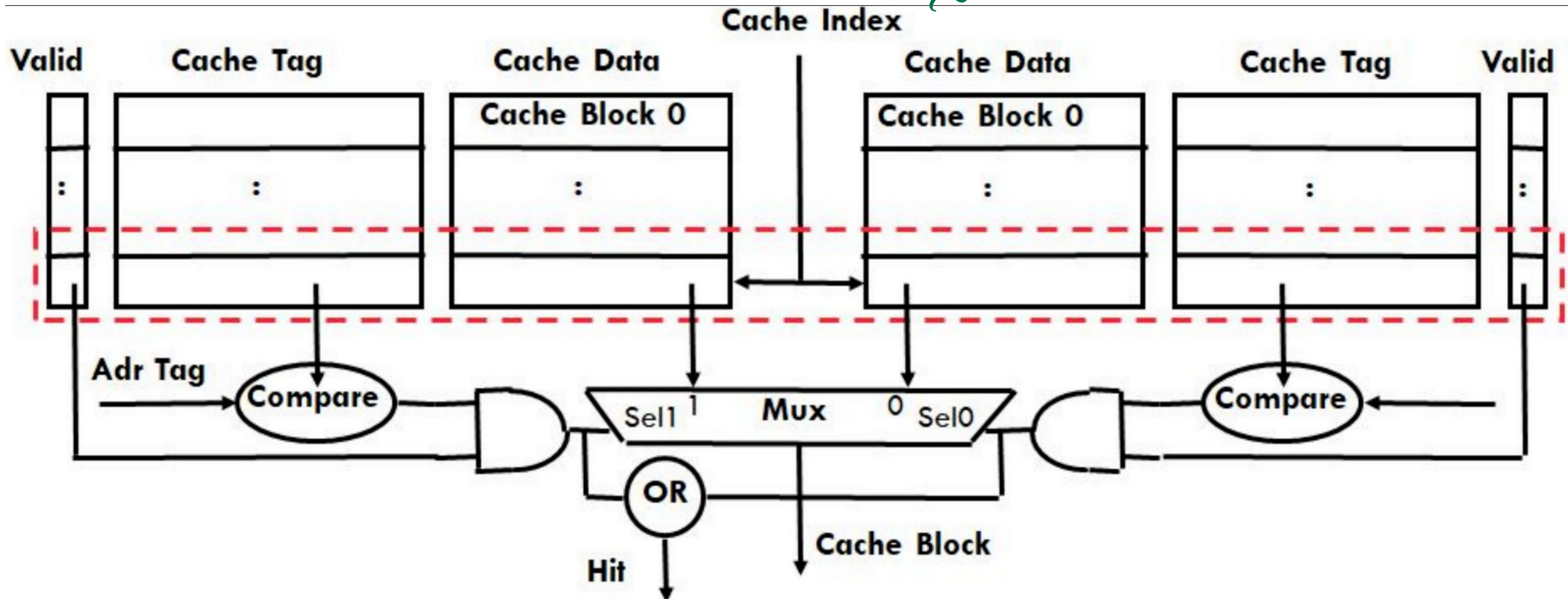
$N=32$



# N-Way Set Associative Cache

$$1 < N < 32$$

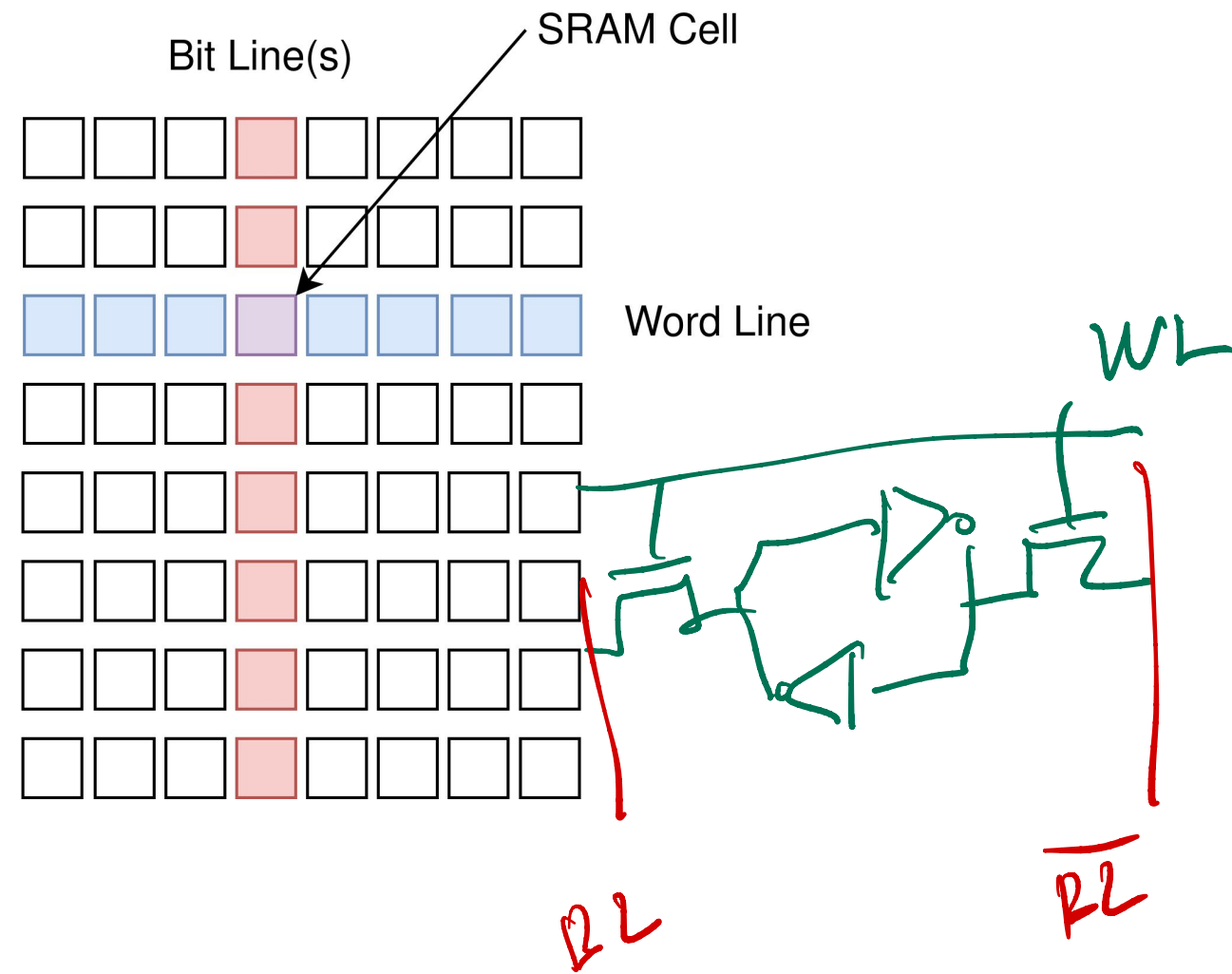
$$N=2$$



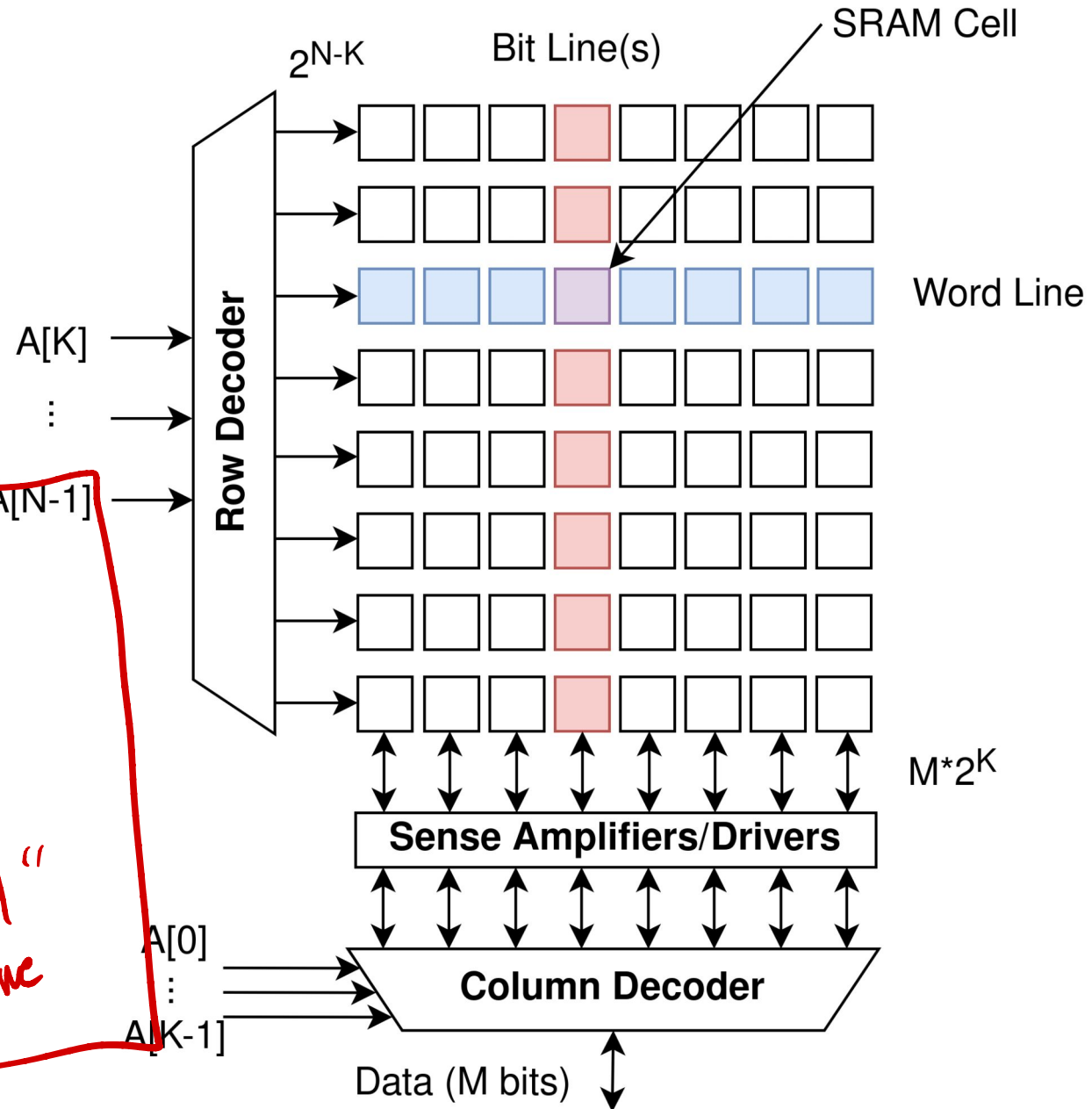
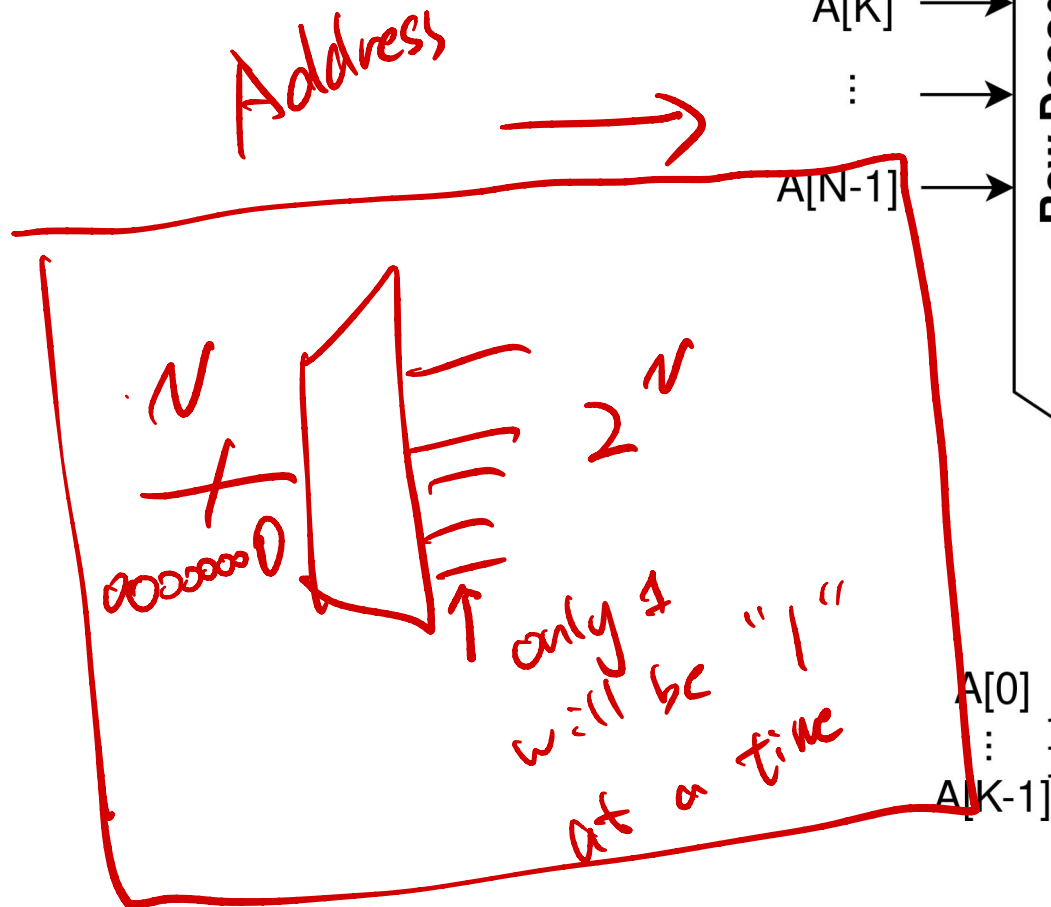


# SRAM Decoders

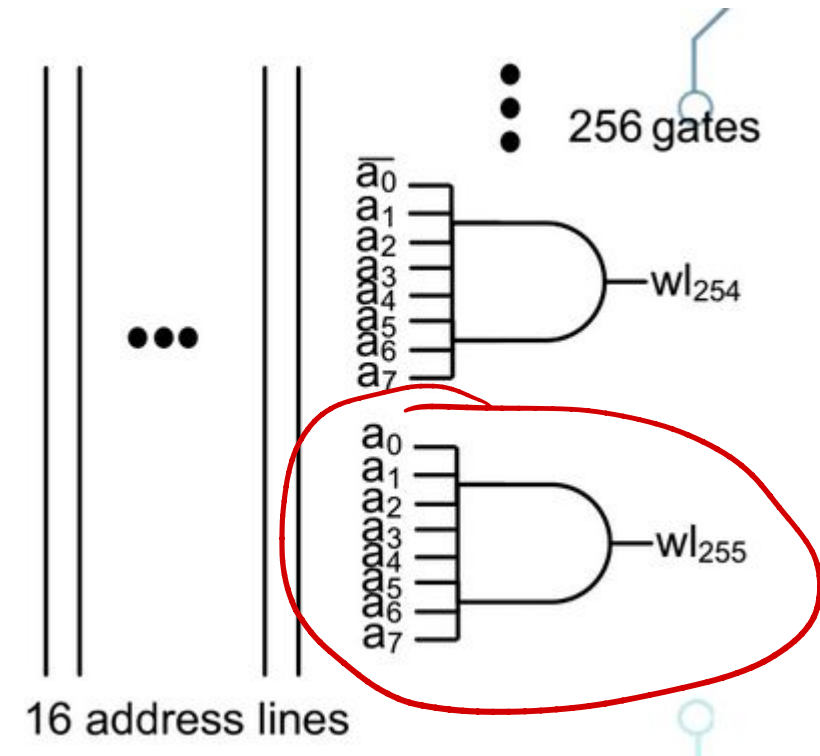
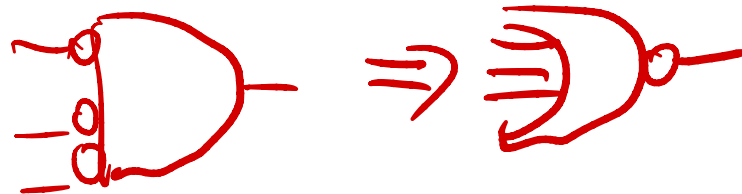
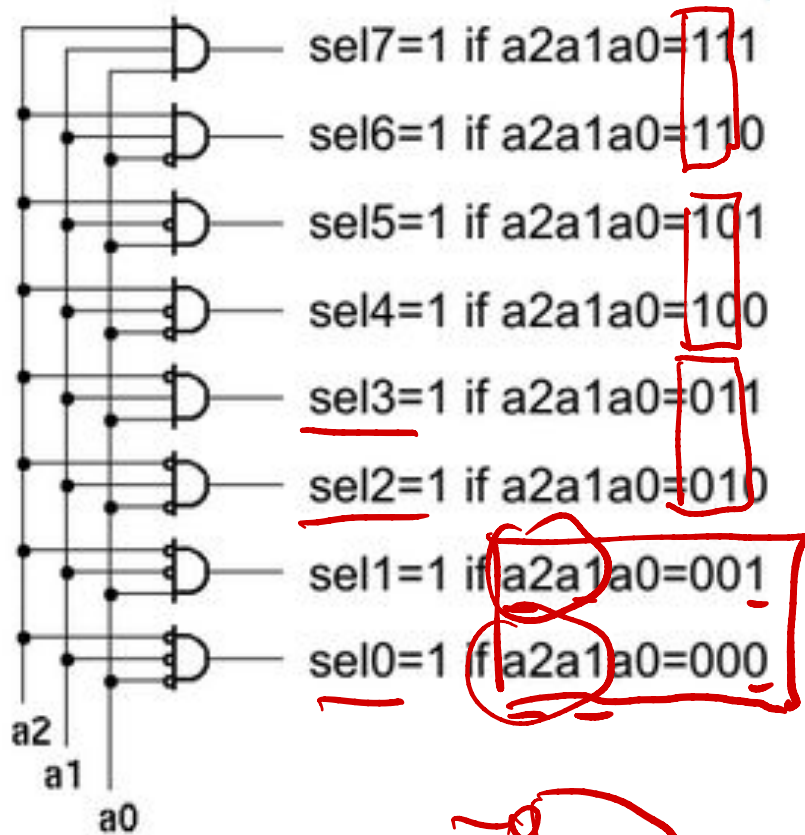
# SRAM Structure:



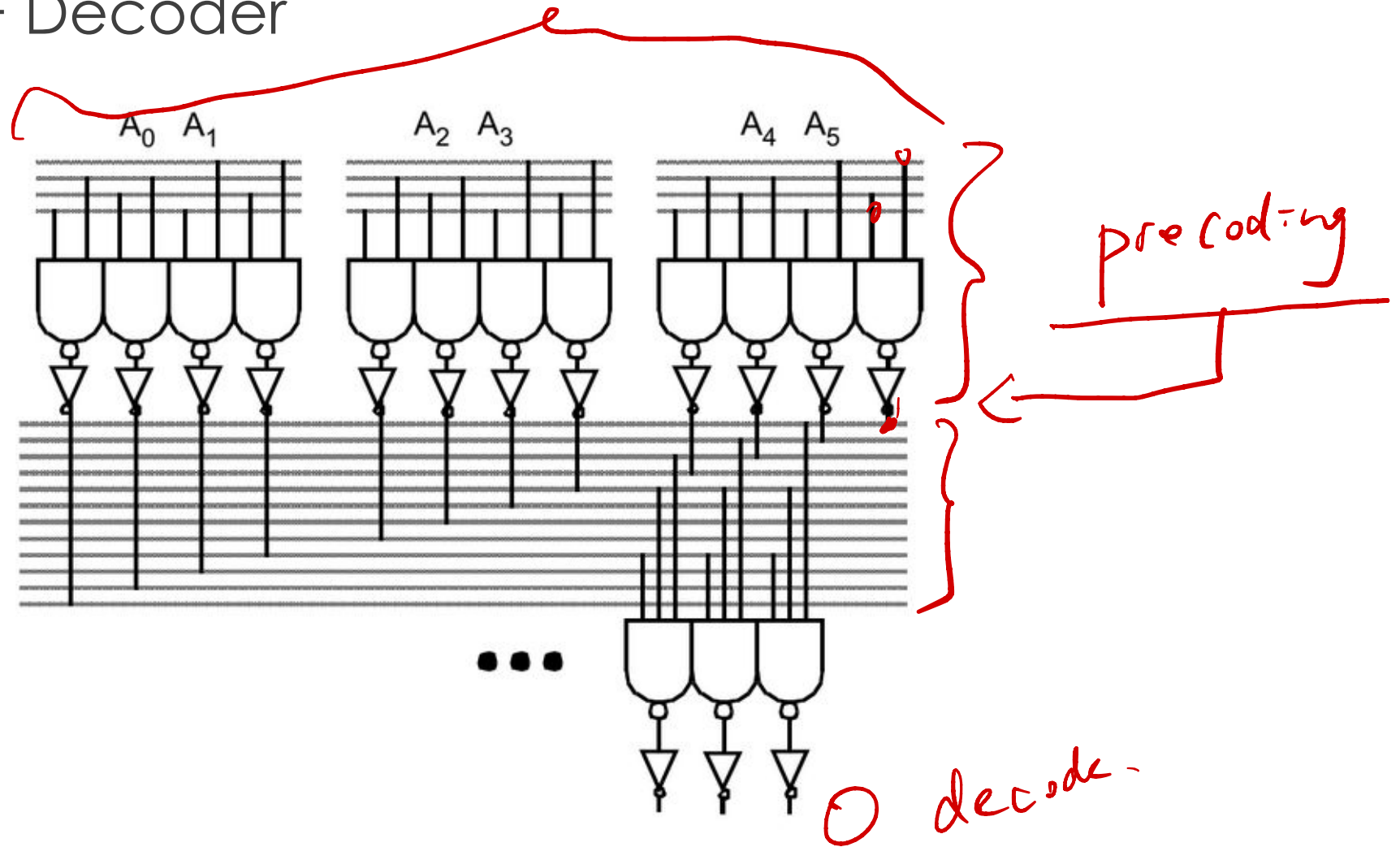
# SRAM Structure:



# Row Decoder: Naive Implementation



## Predecoder + Decoder

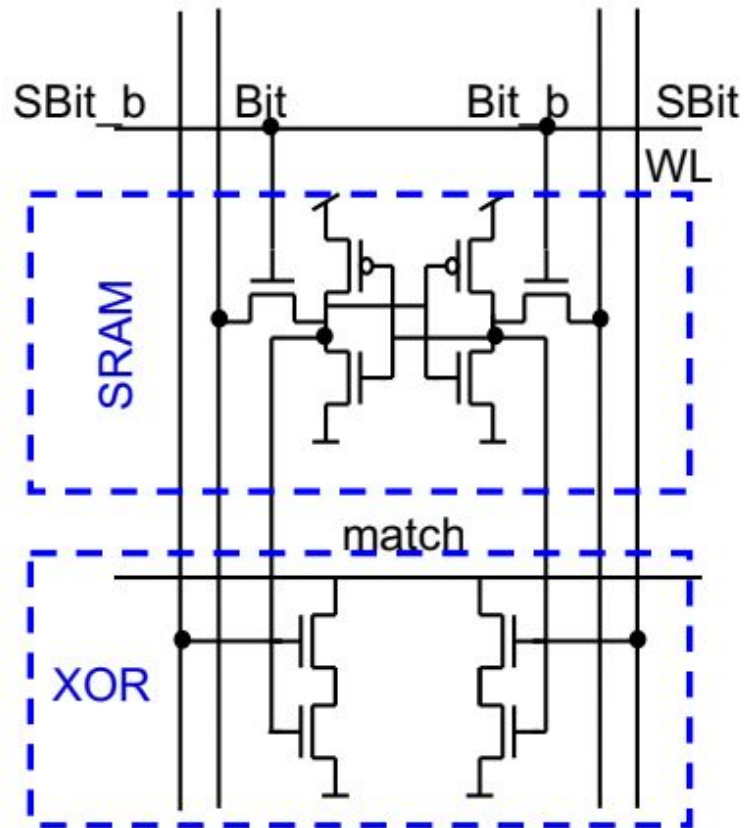


# Other Memories

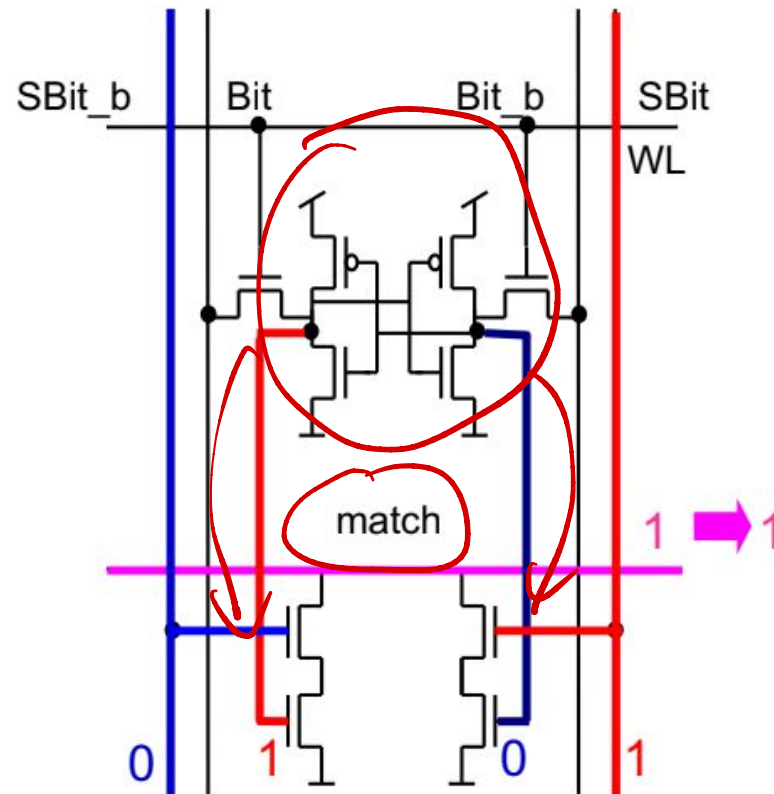
# Content Addressable Memory (CAM)

$$1 \oplus 1 = 0$$

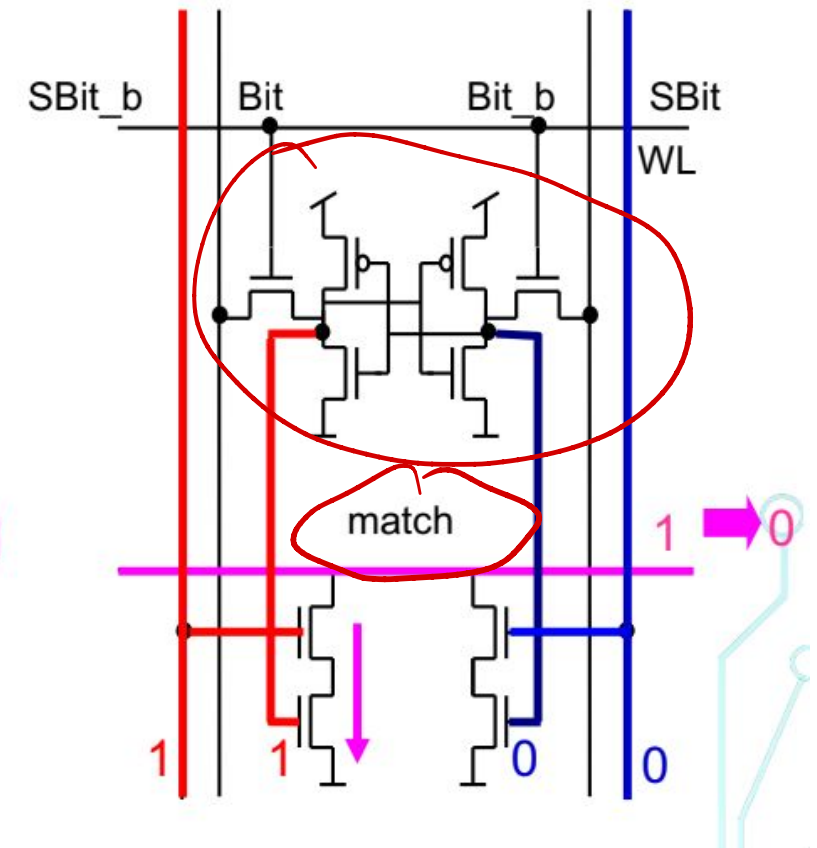
$$1 \oplus 0 = 1$$



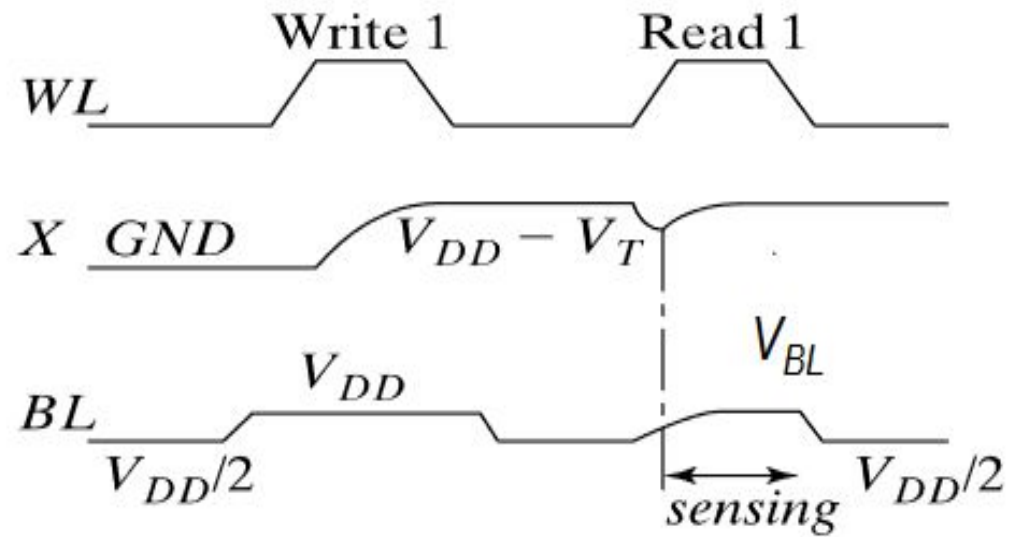
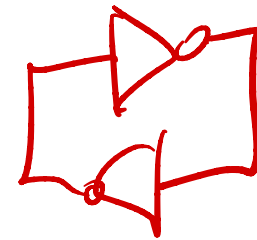
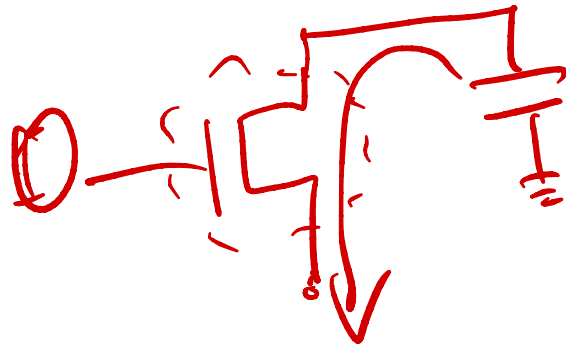
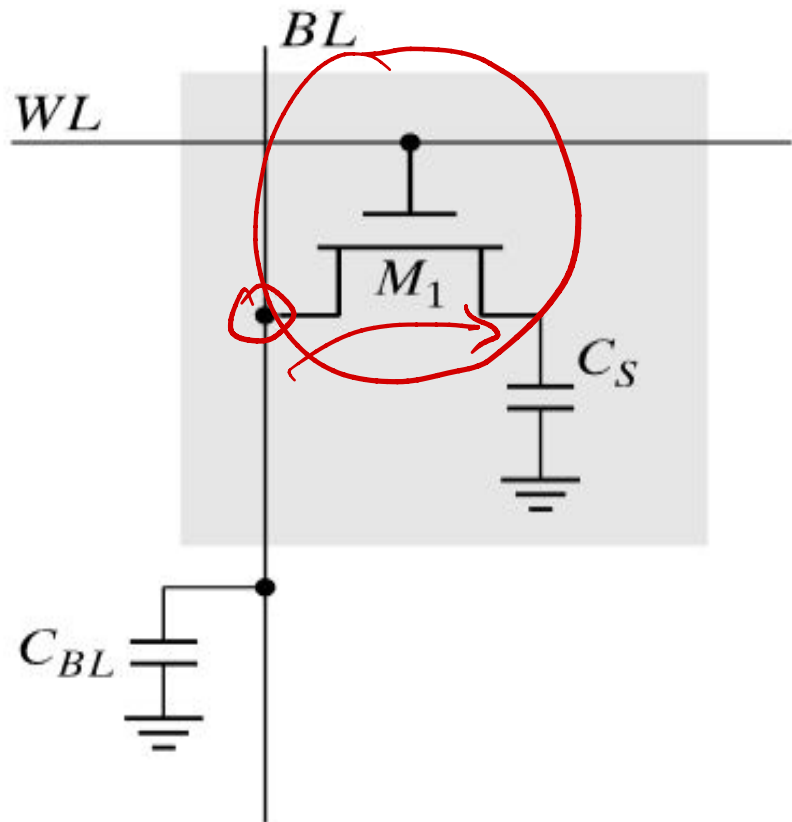
Match



Mismatch



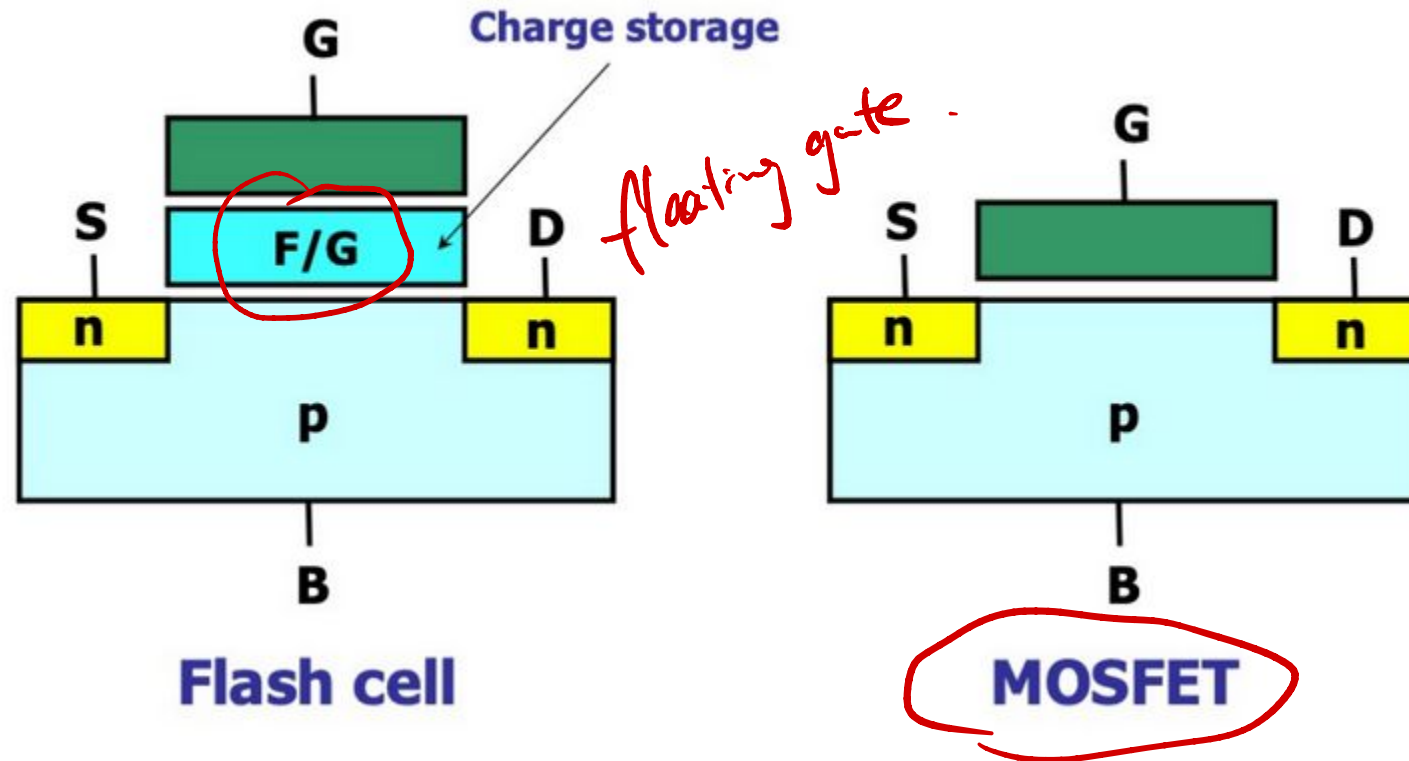
# DRAM



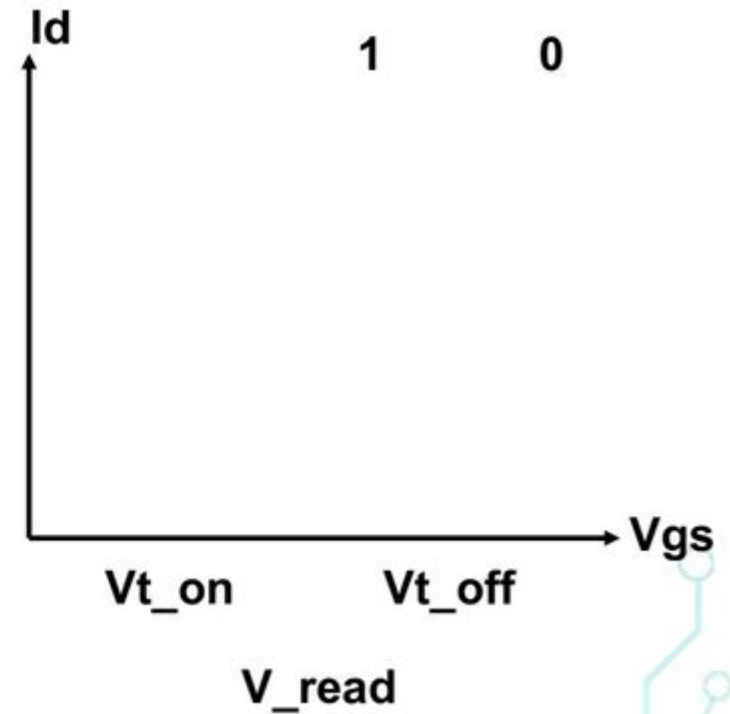
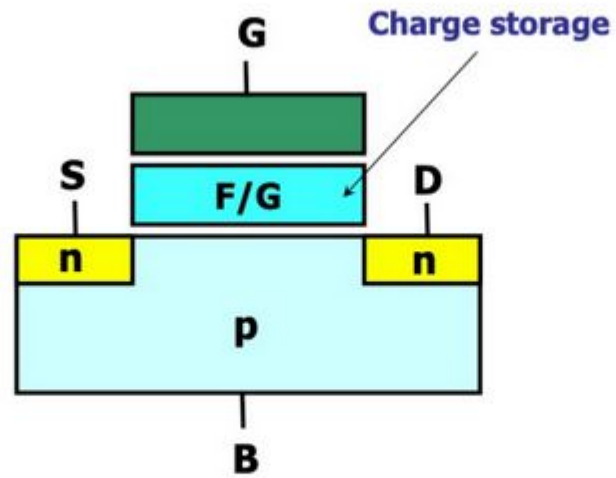
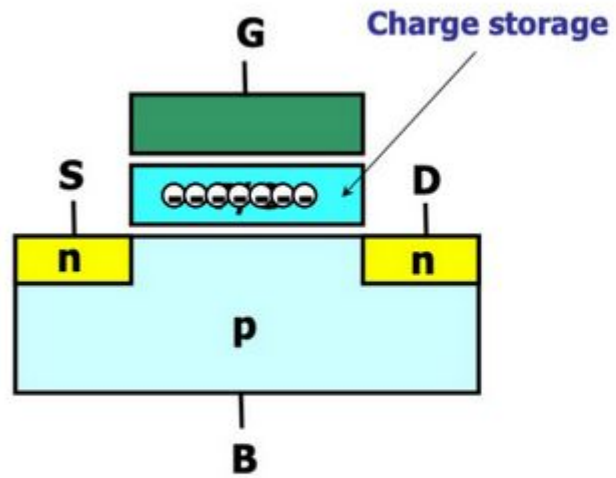
$$V_{BIT} = 0 \text{ or } (V_{DD} - V_T)$$



# Flash Overview

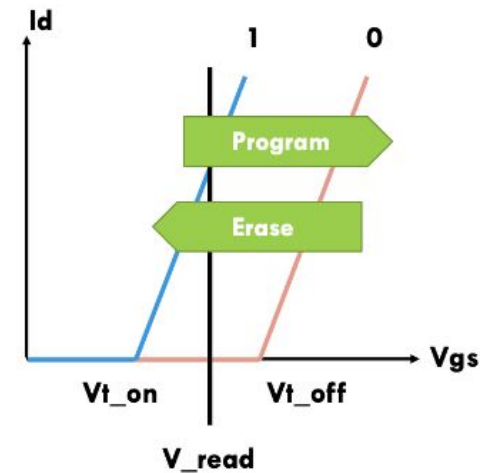
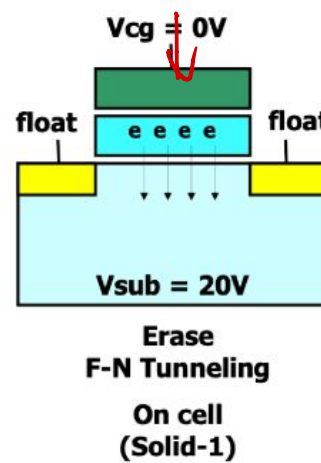
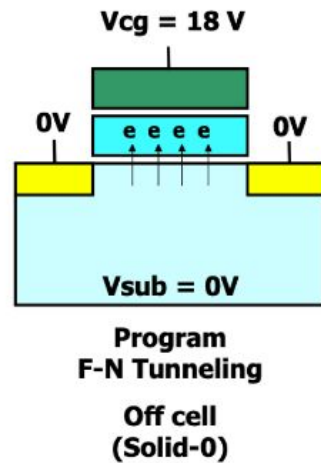


# Flash Overview



# Flash Write

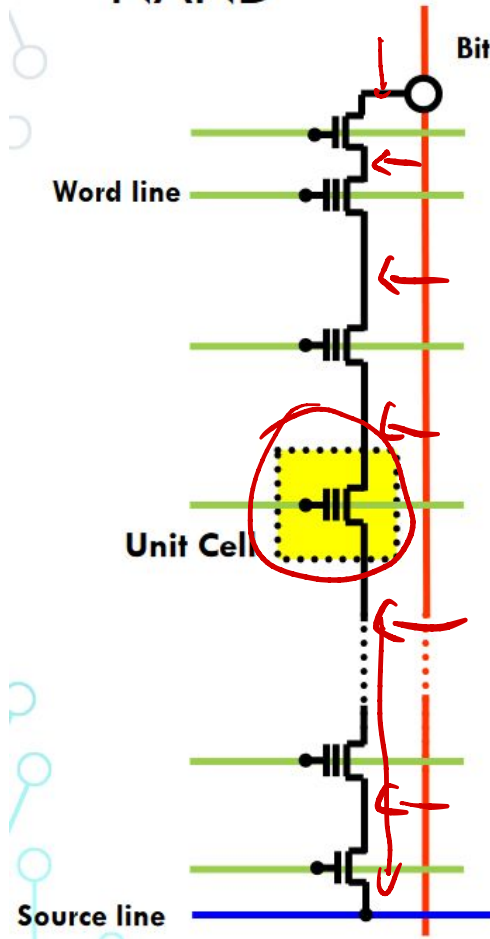
- Step 1: Erasing.
  - Erase all the FG transistors to set them to 1
  - Apply a negative voltage to the gate -> Electrons flow from the floating gate to the substrate.
- Step 2: Programming
  - Reprogram the appropriate FG transistors to set them to 0
  - Apply a high voltage to the gate -> Electrons are tunneled onto the floating gate.



# NAND vs NOR Flash



## • NAND

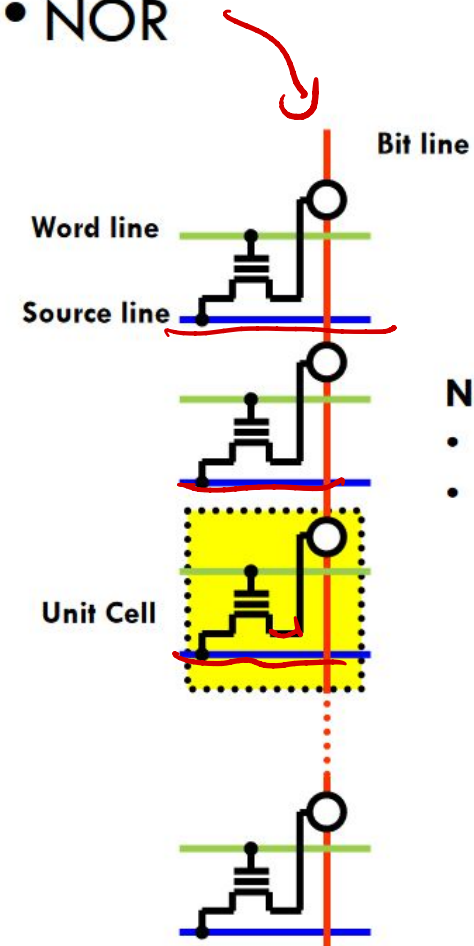


### NAND:

- High Density
- Used for data storage
  - USB drives
  - Memory cards
  - SSD



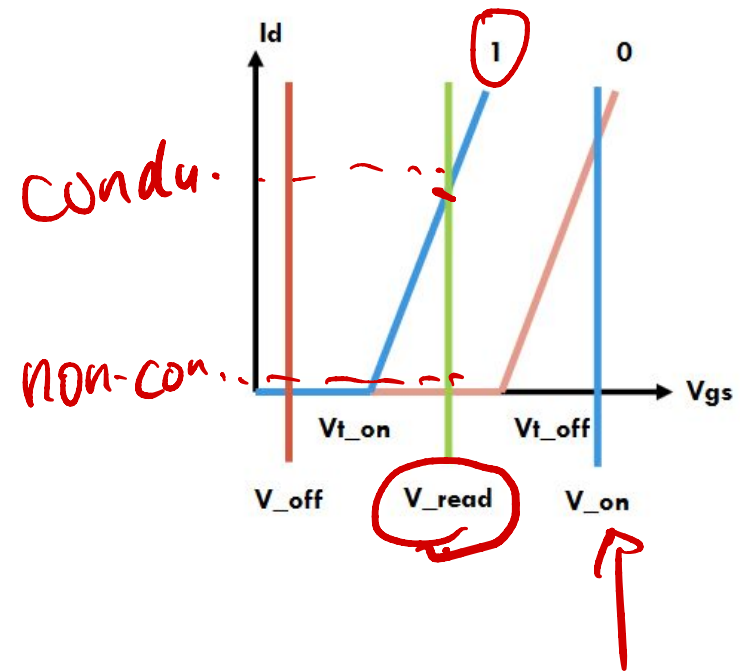
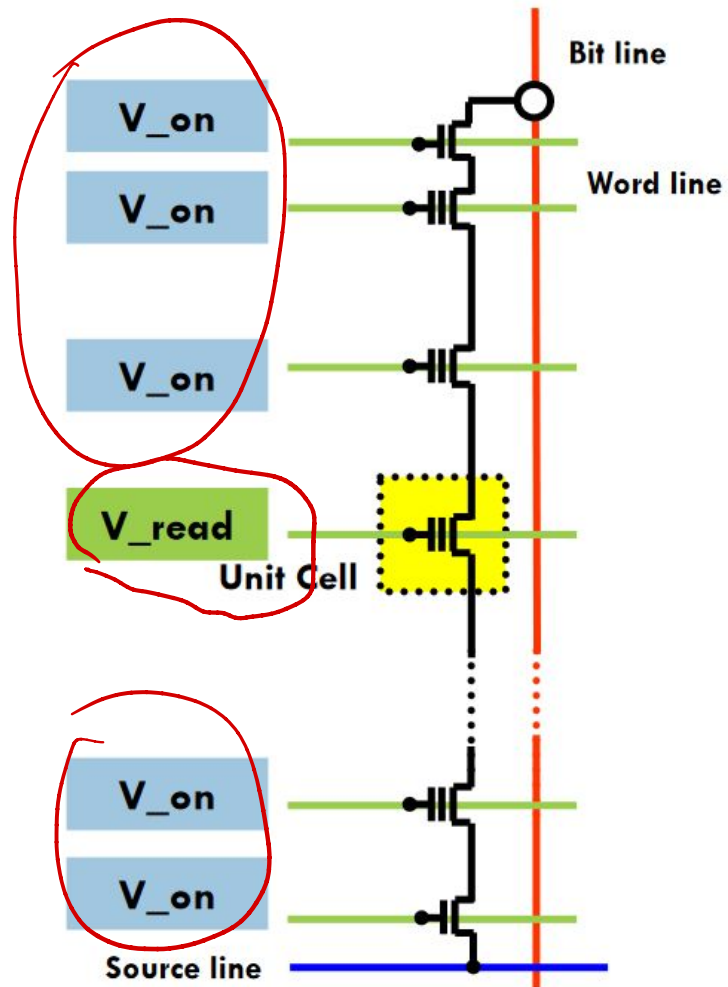
## • NOR



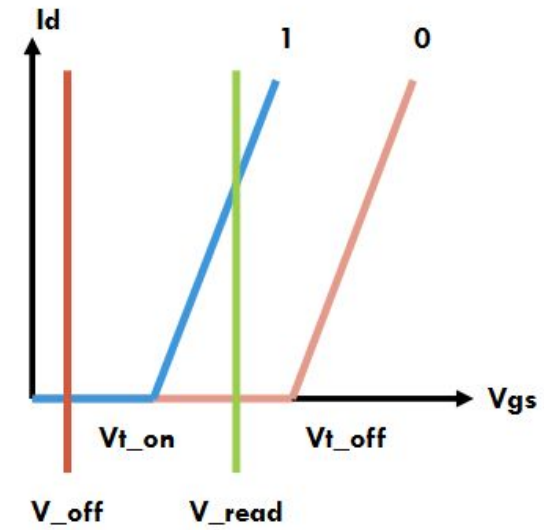
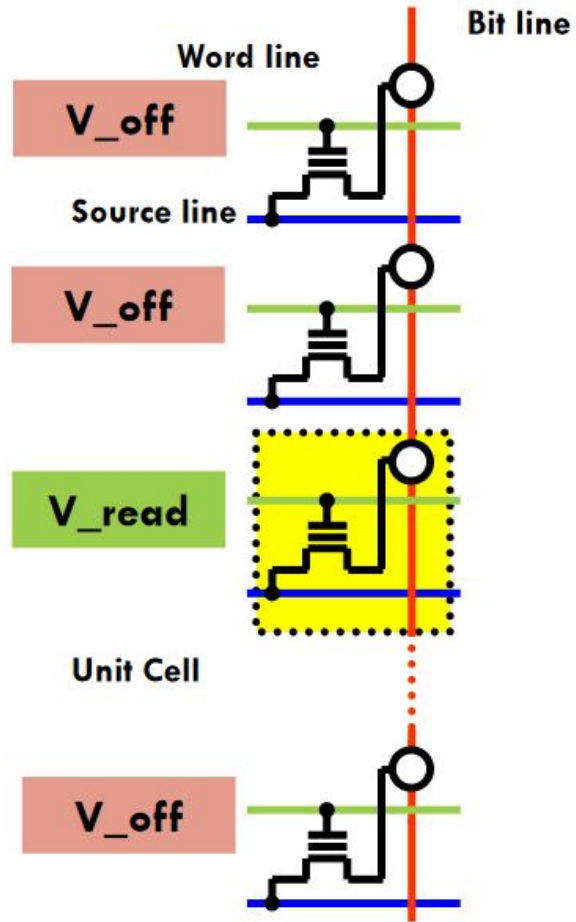
### NOR:

- Lower Latency
- Used for code storage
  - Embedded systems

# NAND Flash Read



# NOR Flash Read



# Questions?